











**TPS84410** ZHCS434C - SEPTEMBER 2011-REVISED APRIL 2018

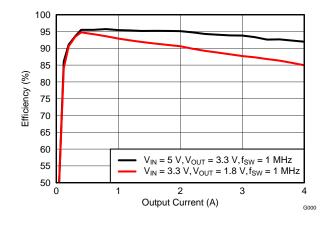
## TPS84410 2.95V 至 6V 输入、4A 同步降压集成式电源解决方案

### 特性

- 完整的集成式电源解决方案可实现 小尺寸和扁平设计
- 效率高达 96%
- 宽输出电压调节范围 0.8V 至 3.6V, 基准精度为 ±1%
- 可调开关频率 (500kHz 至 2MHz)
- 与外部时钟同步
- 可调慢速启动
- 输出电压排序/跟踪
- 电源正常输出
- 可编程欠压锁定 (UVLO)
- 输出过流保护
- 过热保护
- 运行温度范围: -40°C 至 85°C
- 增强的散热性能: 12°C/W
- 符合 EN55022 B 类辐射标准

#### 应用

- 宽带和通信基础设施
- 自动化测试和医疗设备
- 紧凑型 PCI/PCI 快速接口/PXI 快速接口
- DSP 和 FPGA 负载点 应用
- 高密度分布式电源系统

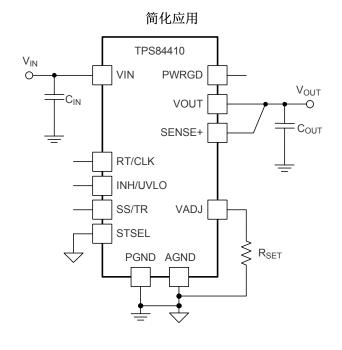


### 3 说明

TPS84410RKG 是一个简单易用的集成式电源解决方 案,它在一个小外形尺寸的 BQFN 封装内整合了一个 带有功率 MOSFET 的 4A 直流/直流转换器、一个电感 器以及多个无源器件。此整体电源解决方案仅需3个 外部组件,并省去了环路补偿和磁性元件选择过程。

9 x 11 x 2.8mm BQFN 封装能轻松焊接到印制电路板 上,并且可实现效率高于90%的紧凑型负载点设计且 结至环境的热阻抗仅为 12°C/W 的出色功率耗散。在 环境温度为 85°C 且无气流的情况下,该器件可提供 4A 的满额输出电流。

TPS84410 提供了灵活且功能完善的离散式负载点设 计,是为高性能 DSP 和 FPGA 供电的理想选择。先进 的封装技术可提供一个与标准 QFN 贴装和测试技术兼 容的耐用且可靠的电源解决方案。





### **Specifications**

### Absolute Maximum Ratings<sup>(1)</sup>

over operating temperature range (unless otherwise noted)

				VALUE		
				MIN	UNIT	
	VI	IN, PWRGD		-0.3	7	V
Input Voltage	IN	IH/UVLO, RT/CI	LK	-0.3	3.3	V
input voitage	S	S/TR, STSEL, V	'ADJ	-0.3	3	V
	SI	SENSE+ VADJ rating must also be met		-0.3	VOUT	V
	PI	Н		-0.6	7	V
Output Voltage	PI	PH 10ns Transient		-2	7	V
	V	VOUT		-0.6	VIN	V
V <sub>DIFF</sub> (GND to exposed then	mal pad)			-0.2	0.2	V
Source Current	R.	RT/CLK, INH/UVLO			±100	μΑ
Source Current	PI	PH			Current Limit	Α
	PI	PH Current Lim PH Current Lim	Current Limit	Α		
Sink Current	S	SS/TR			±100	μΑ
	P	WRGD			.3 7 .3 3.3 .3 3.3 .3 3 .3 VOUT .6 7 .2 7 .6 VIN .2 0.2 .±100 .Current Limit .Current Limit .ture Limi	mA
Operating Junction Tempera	ature			-40	125 <sup>(2)</sup>	°C
Storage Temperature				-65	150	°C
Peak Reflow Case Tempera	ture <sup>(3)</sup>				250 <sup>(4)</sup>	°C
Maximum Number of Reflow	s Allowed <sup>(3)</sup>				3 <sup>(4)</sup>	
Mechanical Shock	Mil-STD-883D, M	ethod 2002.3, 1	msec, 1/2 sine, mounted		1500	0
Mechanical Vibration	Mil-STD-883D, M	ethod 2007.2, 2	0-2000Hz		20	G

- Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- See the temperature derating curves in the Typical Characteristics section for thermal information.
- For soldering specifications, refer to the Soldering Requirements for BQFN Packages application note.
- Devices with a date code prior to week 14 2018 (1814) have a peak reflow case temperature of 240°C with a maximum of one reflow.

#### 4.2 Thermal Information

		TPS84410	
	THERMAL METRIC <sup>(1)</sup>	RKG39	UNIT
		39 PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance (2)	12	
ΨЈТ	Junction-to-top characterization parameter <sup>(3)</sup>	2.2	°C/W
ΨЈВ	Junction-to-board characterization parameter <sup>(4)</sup>	9.7	

- For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- The junction-to-ambient thermal resistance,  $\theta_{JA}$ , applies to devices soldered directly to a 100 mm x 100 mm double-sided PCB with 1 oz.
- copper and natural convection cooling. Additional airflow reduces θ<sub>JA</sub>.
   The junction-to-top characterization parameter, ψ<sub>JT</sub>, estimates the junction temperature, T<sub>J</sub>, of a device in a real system, using a procedure described in JESD51-2A (sections 6 and 7). T<sub>J</sub> = ψ<sub>JT</sub> \* Pdis + T<sub>T</sub>; where Pdis is the power dissipated in the device and T<sub>T</sub> is the temperature of the top of the device.
- (4) The junction-to-board characterization parameter,  $\psi_{JB}$ , estimates the junction temperature,  $T_J$ , of a device in a real system, using a procedure described in JESD51-2A (sections 6 and 7).  $T_J = \psi_{JB} * Pdis + T_B$ ; where Pdis is the power dissipated in the device and  $T_B$  is the temperature of the board 1mm from the device.

### 4.3 Package Specifications

	UNIT							
Weight		0.85 grams						
Flammability	Meets UL 94 V-O							
MTBF Calculated reliability	Per Bellcore TR-332, 50% stress, T <sub>A</sub> = 40°C, ground benign	32.8 MHrs						



#### 4.4 Electrical Characteristics

Over -40°C to 85°C free-air temperature, VIN = 3.3 V,  $V_{OUT}$  = 1.8 V,  $I_{OUT}$  = 4A,  $C_{IN1}$  = 47  $\mu F$  ceramic,  $C_{IN2}$  = 220  $\mu F$  poly-tantalum,  $C_{OUT1}$  = 47  $\mu F$  ceramic,  $C_{OUT2}$  = 100  $\mu F$  poly-tantalum (unless otherwise noted)

	PARAMETER	T	EST CONDITIONS		MIN	TYP	MAX	UNIT
I <sub>OUT</sub>	Output current	T <sub>A</sub> = 85°C, natural convec	tion		0		4	Α
VIN	Input voltage range	Over I <sub>OUT</sub> range			2.95 <sup>(1)</sup>		6	V
111/1/0	V/INTELLED 16 - 1 - 1 - 4	VIN = increasing				3.05	3.135	.,
UVLO	VIN Undervoltage lockout	VIN = decreasing			2.5	2.75		V
V <sub>OUT(adj)</sub>	Output voltage adjust range	Over I <sub>OUT</sub> range			0.8		3.6	V
	Set-point voltage tolerance	T <sub>A</sub> = 25°C, I <sub>OUT</sub> = 0A					±1.0% <sup>(2)</sup>	
	Temperature variation	$40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}, \ \text{I}_{\text{OUT}} = 0\text{A}$			±0.3%			
$V_{OUT}$	Line regulation	Over VIN range, T <sub>A</sub> = 25°0	C, I <sub>OUT</sub> = 0A			±0.1%		
	Load regulation	Over I <sub>OUT</sub> range, T <sub>A</sub> = 25°	nge, T <sub>A</sub> = 25°C			±0.1%		
	Total output voltage variation	ncludes set-point, line, load, and temperature variation				±1.5% <sup>(2)</sup>		
			V <sub>OU</sub> -	r = 3.3V, f <sub>SW</sub> = 1 MHz		95%		
			V <sub>OU</sub>	r = 2.5V, f <sub>SW</sub> = 1 MHz		93%		
				r = 1.8V, f <sub>SW</sub> = 1 MHz		91%		
		VIN = 5 V	V <sub>OU</sub>	<sub>Γ</sub> = 1.5V, f <sub>SW</sub> = 1 MHz		89%		
	η Efficiency	I <sub>O</sub> = 2 A		= 1.2V, f <sub>SW</sub> =750 kHz		87%		
				= 1.0V, f <sub>SW</sub> = 650 kHz		85%		
η				= 0.8V, f <sub>SW</sub> = 650 kHz		84%		
		VIN = 3.3V	V <sub>OUT</sub> = 1.8V, f <sub>SW</sub> = 1 MHz			90%		
		I <sub>O</sub> = 2 A		r = 1.5V, f <sub>SW</sub> = 1 MHz		88%		
				= 1.2V, f <sub>SW</sub> = 750 kHz		87%		
				= 1.0V, f <sub>SW</sub> = 650 kHz		84%		
		$V_{OUT} = 0.8V$ , $f_{SW} = 650 \text{ kHz}$				82%		
	Output voltage ripple	20 MHz bandwith				9		$mV_{PP}$
I <sub>LIM</sub>	Overcurrent threshold					7		Α
				Recovery time		80		μs
	Transient response	1.0 A/µs load step from 1/	A to 3A	V <sub>OUT</sub> over/undershoot		90		mV
V <sub>INH-H</sub>	11770 ( )	Inhibit High Voltage				1.25	Open (3)	.,
V <sub>INH-L</sub>	Inhibit Control	Inhibit Low Voltage			-0.3		1.0	V
I <sub>I(stby)</sub>	Input standby current	INH pin to AGND				70	100	μΑ
		\/		Good		93%		
	DIA/DOD TI	V <sub>OUT</sub> rising		Fault		107%		
Power Good	PWRGD Thresholds	) ( III )		Fault		91%		
Ooou		V <sub>OUT</sub> falling		Good		105%		
	PWRGD Low Voltage	I(PWRGD) = 0.33 mA					0.3	V
f <sub>SW</sub>	Switching frequency	Over VIN and I <sub>OUT</sub> ranges	, RT/CLK pin OPEN		400	500	600	kHz
f <sub>CLK</sub>	Synchronization frequency				500		2000	kHz
V <sub>CLK-H</sub>	CLK High-Level Threshold				2.2		3.3	V
V <sub>CLK-L</sub>	CLK Low-Level Threshold	CLK Control			-0.3		0.4	V
	CLK Pulse Width	1			75 <sup>(4)</sup>			ns
	The served Objected	Thermal shutdown				175		°C
	Thermal Shutdown	Thermal shutdown hysteresis				15		°C

- The minimum VIN depends on VOUT and the switching frequency. Please refer to Table 8 for operating limits.
- The stated limit of the set-point voltage tolerance includes the tolerance of both the internal voltage reference and the internal adjustment resistor. The overall output voltage tolerance will be affected by the tolerance of the external R<sub>SET</sub> resistor.
- This control pin has an internal pullup. Do not place an external pull-up resistor on this pin. If this pin is left open circuit, the device operates when input power is applied. A small low-leakage MOSFET is recommended for control. See the application section for further
- The maximum synchronization clock pulse width is dependant on VIN, V<sub>OUT</sub>, and the synchronization frequency. See the Synchronization (CLK) section for more information.



### **Electrical Characteristics (continued)**

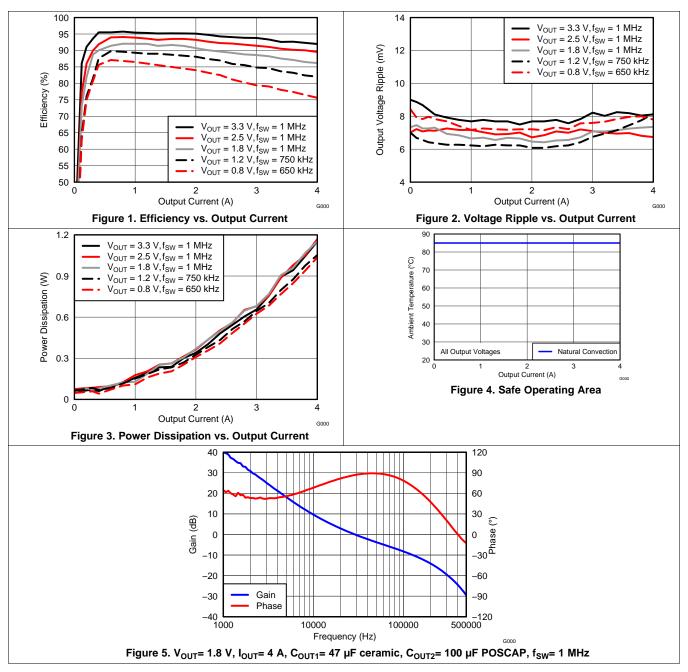
Over -40°C to 85°C free-air temperature, VIN = 3.3 V,  $V_{OUT}$  = 1.8 V,  $I_{OUT}$  = 4A,  $C_{IN1}$  = 47  $\mu$ F ceramic,  $C_{IN2}$  = 220  $\mu$ F poly-tantalum,  $C_{OUT1}$  = 47  $\mu$ F ceramic,  $C_{OUT2}$  = 100  $\mu$ F poly-tantalum (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
C <sub>IN</sub> External input capacitance	Ceramic	47 (5)				
	External input capacitance	Non-ceramic		220(5)		μF
		Ceramic	47 (6)	150	650 <sup>(7)</sup>	
C <sub>OUT</sub> E	External output capacitance	Non-ceramic		100 <sup>(6)</sup>	2000 <sup>(7)</sup>	μF
		Equivalent series resistance (ESR)			25	mΩ

- (5) A minimum of 47μF of ceramic capacitance is required across the input for proper operation. Locate the capacitor close to the device. An additional 220μF of bulk capacitance is recommended. See Table 6 for more details.
- (6) The amount of required output capacitance varies depending on the output voltage (see Table 4). The amount of required capacitance must include at least 47μF of ceramic capacitance. Locate the capacitance close to the device. Adding additional capacitance close to the load improves the response of the regulator to load transients. See Table 4 and Table 6 for more details.
- (7) When using both ceramic and non-ceramic output capacitance, the combined maximum must not exceed 2200µF.



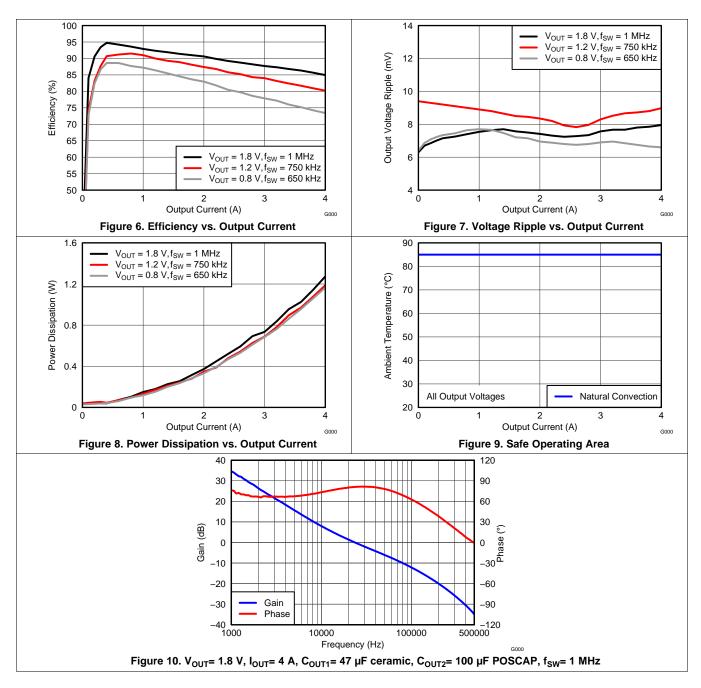
### 4.5 Typical Characteristics (VIN = 5 V) (8) (9)



- (8) The electrical characteristic data has been developed from actual products tested at 25°C. This data is considered typical for the converter. Applies to Figure 1, Figure 2, and Figure 3.
- (9) The temperature derating curves represent the conditions at which internal components are at or below the manufacturer's maximum operating temperatures. Derating limits apply to devices soldered directly to a 100 mm × 100 mm double-sided PCB with 1 oz. copper. Applies to Figure 4.

# TEXAS INSTRUMENTS

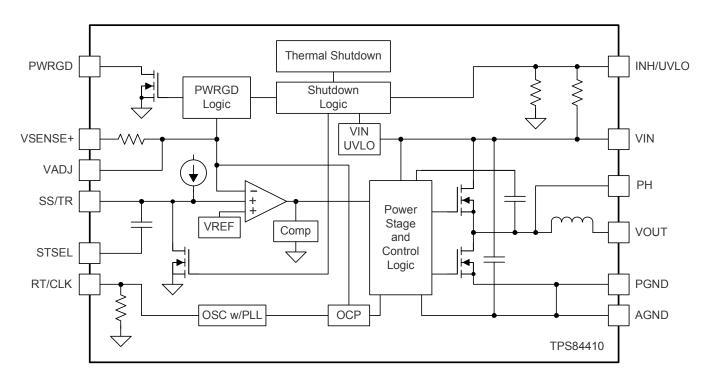
### 4.6 Typical Characteristics (VIN = 3.3 V) (10) (11)



- (10) The electrical characteristic data has been developed from actual products tested at 25°C. This data is considered typical for the converter. Applies to Figure 6, Figure 7, and Figure 8.
- (11) The temperature derating curves represent the conditions at which internal components are at or below the manufacturer's maximum operating temperatures. Derating limits apply to devices soldered directly to a 100 mm x 100 mm double-sided PCB with 1 oz. copper. Applies to Figure 9.



## 5 Functional Block Diagram



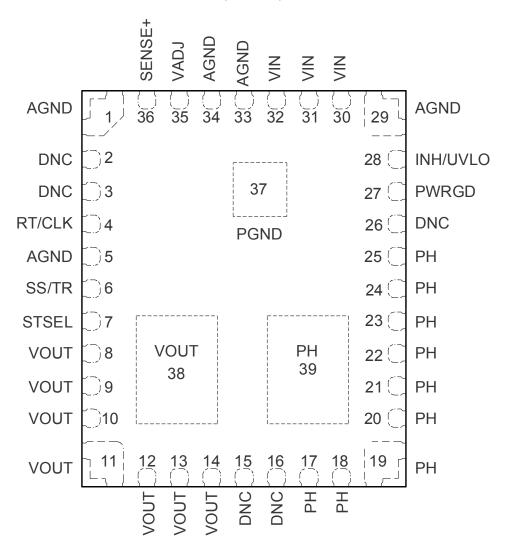


### **Table 1. Pin Functions**

TER	MINAL	DESCRIPTION					
NAME	NO.						
	1	Zara VDC reference for the angles control size its. These size should be consected discostly to the DCD					
	5	Zero VDC reference for the analog control circuitry. These pins should be connected directly to the PCB analog ground plane. Not all pins are connected together internally. All pins must be connected together and the connected together a					
AGND	29	externally with a copper plane or pour directly under the module. Connect the AGND copper area to the					
	33	PGND copper area at a single point; directly at the pin 37 PowerPAD using multiple vias. See the recommended layout in Figure 34.					
	34	- Soon Market Ma					
PowerPAD (PGND)	37	This pad provides both an electrical and thermal connection to the PCB. This pad should be connected directly to the PCB power ground plane using multiple vias for good electrical and thermal performance. The same vias should also be used to connect to the PCB analog ground plane. See the recommended layout in Figure 34.					
	2						
	3						
DNC	15	Do not connect. Do not connect these pins to AGND, to another DNC pin, or to any other voltage. These pins are connected to internal circuitry. Each pin must be soldered to an isolated pad.					
	16	pins are connected to internal circulary. Each pin must be soldered to an isolated pad.					
	26						
INH/UVLO	28	Inhibit and UVLO adjust pin. Use an open drain or open collector output logic to control the INH function. A resistor between this pin and AGND adjusts the UVLO voltage.					
	17						
	18						
	19						
	20						
DU	21	Phase switch node. These pins should be connected by a small copper island under the device for thermal					
PH	22	relief. Do not connect any external component to this pin or tie it to a pin of another function.					
	23						
	24						
	25						
	39						
PWRGD	27	Power good fault pin. Asserts low if the output voltage is out of tolerance. A pull-up resistor is required.					
RT/CLK	4	This pin automatically selects between RT mode and CLK mode. An external timing resistor adjusts the switching frequency of the device. In CLK mode, the device synchronizes to an external clock.					
SENSE+	36	Remote sense connection. Connect this pin to VOUT at the load for improved regulation. This pin must be connected to VOUT at the load, or at the module pins.					
SS/TR	6	Slow-start and tracking pin. Connecting an external capacitor to this pin adjusts the output voltage rise time. A voltage applied to this pin allows for tracking and sequencing control.					
STSEL	7	Slow-start or track feature select. Connect this pin to AGND to enable the internal SS capacitor with a SS interval of approximately 1.1 ms. Leave this pin open to enable the TR feature.					
VADJ	35	Connecting a resistor between this pin and AGND sets the output voltage above the 0.8V default voltage.					
	30	The section is a section of the section of the polygon of the section of the polygon of the section of the sect					
VIN	31	The positive input voltage power pins, which are referenced to PGND. Connect external input capacitance between these pins and the PGND plane, close to the device.					
	32	, , , , , , , , , , , , , , , , , , , ,					
	8						
	9						
	10						
VOUT	11	Output voltage. Connect output capacitors between these pins and the PGND plane, close to the device.					
VOO1	12	Output voitage. Connect output capacitors between these pins and the POND plane, close to the device.					
	13						
	14						
	38						









### 6 Application Information

### 6.1 Adjusting The Output Voltage

The VADJ control sets the output voltage of the TPS84410. The output voltage adjustment range is from 0.8V to 3.6V. The adjustment method requires the addition of  $R_{SET}$ , which sets the output voltage, the connection of SENSE+ to VOUT, and in some cases  $R_{RT}$  which sets the switching frequency. The  $R_{SET}$  resistor must be connected directly between the VADJ (pin 35) and AGND (pin 33 & 34). The SENSE+ pin (pin 36) must be connected to VOUT either at the load for improved regulation or at VOUT of the module. The  $R_{RT}$  resistor must be connected directly between the RT/CLK (pin 4) and AGND (pins 33 & 34).

Table 2 gives the standard external  $R_{\text{SET}}$  resistor for a number of common bus voltages, along with the recommended  $R_{\text{RT}}$  resistor for that output voltage.

Table 2. Standard R<sub>SET</sub> Resistor Values for Common Output Voltages

RESISTORS	OUTPUT VOLTAGE V <sub>OUT</sub> (V)							
	0.8	1.2	1.5	1.8	2.5	3.3		
R <sub>SET</sub> (kΩ)	open	2.87	1.65	1.15	0.673	0.459		
R <sub>RT</sub> (kΩ)	1200	715	348	348	348	348		

For other output voltages, the value of the required resistor can either be calculated using the following formula, or simply selected from the range of values given in Table 3.

$$R_{SET} = \frac{1.43}{\left(\left(\frac{V_{OUT}}{0.803}\right) - 1\right)} (k\Omega)$$
(1)

Table 3. Standard R<sub>SFT</sub> Resistor Values

	351										
V <sub>OUT</sub> (V)	R <sub>SET</sub> (kΩ)	$R_{RT}(k\Omega)$	f <sub>SW</sub> (kHz)	V <sub>OUT</sub> (V)	R <sub>SET</sub> (kΩ)	$R_{RT}(k\Omega)$	f <sub>SW</sub> (kHz)				
0.8	open	1200	650	2.3	0.768	348	1000				
0.9	11.8	1200	650	2.4	0.715	348	1000				
1.0	5.83	1200	650	2.5	0.673	348	1000				
1.1	3.83	1200	650	2.6	0.634	348	1000				
1.2	2.87	715	750	2.7	0.604	348	1000				
1.3	2.32	715	750	2.8	0.576	348	1000				
1.4	1.91	715	750	2.9	0.549	348	1000				
1.5	1.65	348	1000	3.0	0.523	348	1000				
1.6	1.43	348	1000	3.1	0.499	348	1000				
1.7	1.27	348	1000	3.2	0.475	348	1000				
1.8	1.15	348	1000	3.3	0.459	348	1000				
1.9	1.05	348	1000	3.4	0.442	348	1000				
2.0	0.953	348	1000	3.5	0.422	348	1000				
2.1	0.845	348	1000	3.6	0.412	348	1000				
2.2	0.825	348	1000								



### 6.2 Capacitor Recommendations For The TPS84410 Power Supply

### 6.2.1 Capacitor Technologies

### 6.2.1.1 Electrolytic, Polymer-Electrolytic Capacitors

When using electrolytic capacitors, high-quality, computer-grade electrolytic capacitors are recommended. Polymer-electrolytic type capacitors are recommended for applications where the ambient operating temperature is less than 0°C. The Sanyo OS-CON capacitor series is suggested due to the lower ESR, higher rated surge, power dissipation, ripple current capability, and small package size. Aluminum electrolytic capacitors provide adequate decoupling over the frequency range of 2 kHz to 150 kHz, and are suitable when ambient temperatures are above 0°C.

#### 6.2.1.2 Ceramic Capacitors

The performance of aluminum electrolytic capacitors is less effective than ceramic capacitors above 150 kHz. Multilayer ceramic capacitors have a low ESR and a resonant frequency higher than the bandwidth of the regulator. They can be used to reduce the reflected ripple current at the input as well as improve the transient response of the output.

### 6.2.1.3 Tantalum, Polymer-Tantalum Capacitors

Polymer-tantalum type capacitors are recommended for applications where the ambient operating temperature is less than 0°C. The Sanyo POSCAP series and Kemet T530 capacitor series are recommended rather than many other tantalum types due to their lower ESR, higher rated surge, power dissipation, ripple current capability, and small package size. Tantalum capacitors that have no stated ESR or surge current rating are not recommended for power applications.

#### 6.2.2 Input Capacitor

The TPS84410 requires a minimum input capacitance of 47  $\mu$ F of ceramic capacitance. An additional 220  $\mu$ F polymer-tantalum capacitor is recommended for applications with transient load requirements. The combined ripple current rating of the input capacitors must be at least 2000 mArms. Table 6 includes a preferred list of capacitors by vendor. For applications where the ambient operating temperature is less than 0°C, an additional 1  $\mu$ F, X5R or X7R ceramic capacitor placed between VIN and AGND is recommended.

#### 6.2.3 Output Capacitor

The required output capacitance is determined by the output voltage of the TPS84410. See Table 4 for the amount of required capacitance. The required output capacitance must include at least one 47  $\mu$ F ceramic capacitor. For applications where the ambient operating temperature is less than 0°C, an additional 100  $\mu$ F polymer-tantalum capacitor is recommended. When adding additional non-ceramic bulk capacitors, low-ESR devices like the ones recommended in Table 6 are required. The required capacitance above the minimum is determined by actual transient deviation requirements. See Table 5 for typical transient response values for several output voltage, input voltage and capacitance combinations. Table 6 includes a preferred list of capacitors by vendor.

**Table 4. Required Output Capacitance** 

V <sub>OUT</sub> RA	NGE (V)	MINIMUM DECLUDED C (VE)			
MIN	MAX	MINIMUM REQUIRED C <sub>OUT</sub> (μF)			
0.8	< 1.8	147 <sup>(1)</sup>			
1.8	< 3.3	100 <sup>(2)</sup>			
3.3	3.6	47 <sup>(2)</sup>			

Minimum required must include at least 1 x 47 μF ceramic capacitor plus 1 x 100 μF polymer-tantalum capacitor

<sup>(2)</sup> Minimum required must include at least 47 µF of ceramic capacitance.



### **Table 5. Output Voltage Transient Response**

C <sub>IN1</sub> = 1 x 47 μF CERAMIC, C <sub>IN2</sub> = 220 μF POLYMER-TANTALUM, LOAD STEP = 2 A, 1 A/μs										
V <sub>OUT</sub> (V)	V <sub>IN</sub> (V)	C <sub>OUT1</sub> Ceramic	C <sub>OUT2</sub> BULK	VOLTAGE DEVIATION (mV)	PEAK-PEAK (mV)	RECOVERY TIME (µs)				
	3.3	47 µF	100 μF	50	95	60				
0.0	3.3	47 µF	330 μF	45	85	70				
0.8		47 µF	100 μF	45	85	50				
	5	47 µF	330 µF	40	75	65				
3.3	47 µF	100 μF	70	130	80					
	3.3	47 µF	330 µF	55	100	80				
1.2	1.2 5	47 µF	100 μF	60	110	65				
		47 µF	330 µF	50	90	80				
	2.2	47 µF	100 μF	95	185	90				
4.0	3.3	47 µF	330 µF	75	140	110				
1.8	_	47 μF	100 μF	80	160	70				
	5	47 µF	330 µF	65	125	90				
0.5	_	47 µF	100 μF	100	200	80				
2.5	5	2x 47 μF	-	140	270	90				
0.0		47 μF	100 μF	130	255	100				
3.3	5	47 μF	-	200	400	120				

## Table 6. Recommended Input/Output Capacitors<sup>(1)</sup>

			CAP	CAPACITOR CHARACTERISTICS					
VENDOR	SERIES	PART NUMBER	WORKING VOLTAGE (V)	CAPACITANCE (μF)	ESR <sup>(2)</sup> (mΩ)				
Murata	X5R	GRM32ER61C476K	16	47	2				
TDK	X5R	C3225X5R0J107M	6.3	100	2				
Murata	X5R	GRM32ER60J107M	6.3	100	2				
TDK	X5R	C3225X5R0J476K	6.3	47	2				
Murata	X5R	GRM32ER60J476M	6.3	47	2				
Sanyo	POSCAP	10TPE220ML	10	220	25				
Kemet	T520	T520V107M010ASE025	10	100	25				
Sanyo	POSCAP	6TPE100MPB	6.3	100	25				
Sanyo	POSCAP	2R5TPE220M7	2.5	220	7				
Kemet	T530	T530D227M006ATE006	6.3	220	6				
Kemet	T530	T530D337M006ATE010	6.3	330	10				
Sanyo	POSCAP	2TPF330M6	2.0	330	6				
Sanyo	POSCAP	6TPE330MFL	6.3	330	15				

#### (1) Capacitor Supplier Verification

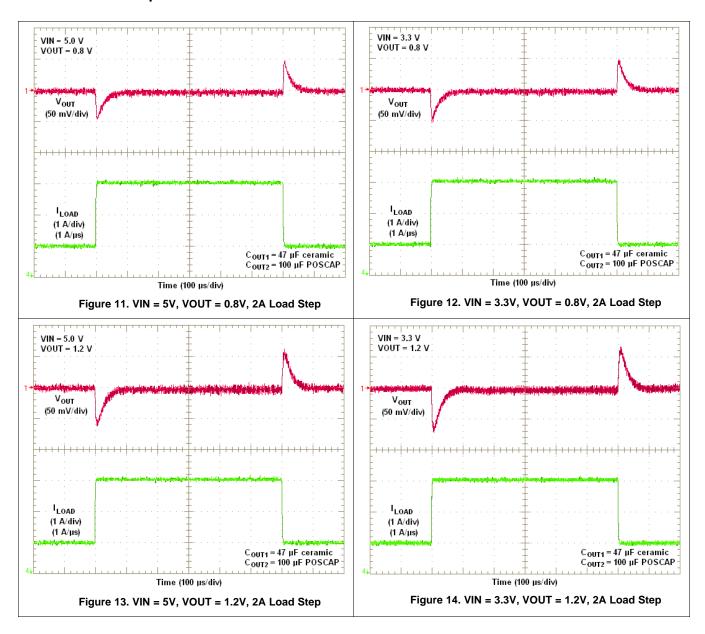
Please verify availability of capacitors identified in this table. RoHS, Lead-free and Material Details

Please consult capacitor suppliers regarding material composition, RoHS status, lead-free status, and manufacturing process requirements.

(2) Maximum ESR @ 100kHz, 25°C.

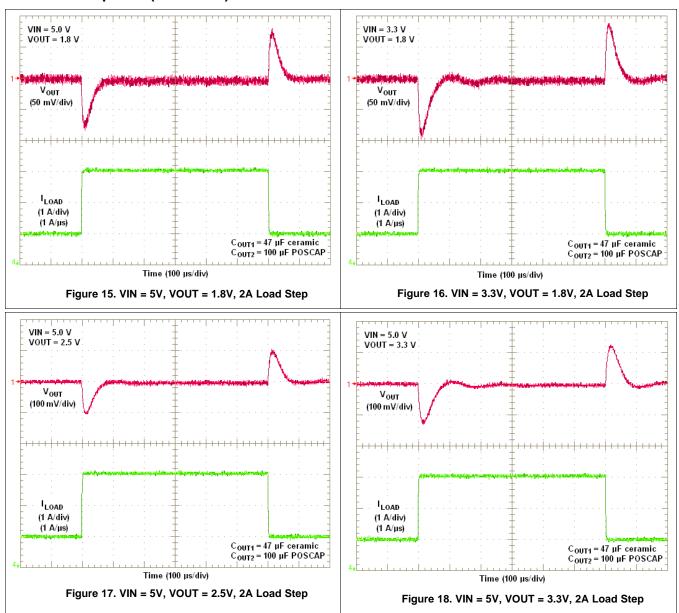


### 6.3 Transient Response



### TEXAS INSTRUMENTS

### **Transient Response (continued)**





### 6.4 Application Schematics

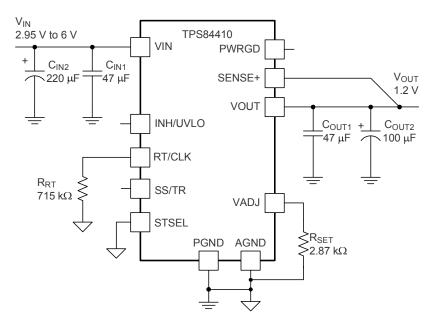


Figure 19. Typical Schematic VIN = 2.95 V to 6.0 V, VOUT = 1.2 V

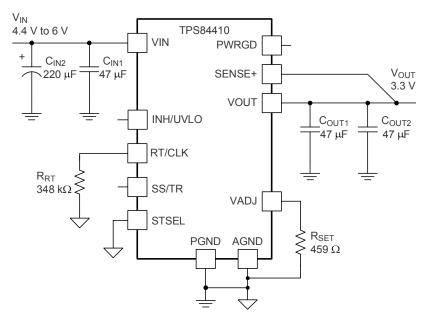


Figure 20. Typical Schematic VIN = 4.4 V to 6.0 V, VOUT = 3.3 V

### 6.5 Power Good (PWRGD)

The PWRGD pin is an open drain output. Once the voltage on the SENSE+ pin is between 93% and 105% of the set voltage, the PWRGD pin pull-down is released and the pin floats. The recommended pull-up resistor value is between 10 k $\Omega$  and 100 k $\Omega$  to a voltage source that is 6 V or less. The PWRGD pin is in a defined state once VIN is greater than 1.2 V, but with reduced current sinking capability. The PWRGD pin achieves full current sinking capability once the VIN pin is above 2.95V. Figure 21 shows the PWRGD waveform during power-up. The PWRGD pin is pulled low when the voltage on SENSE+ is lower than 91% or greater than 107% of the nominal set voltage. Also, the PWRGD pin is pulled low if the input UVLO or thermal shutdown is asserted, or if the INH pin is pulled low.

### 6.6 Power-Up Characteristics

When configured as shown in the front page schematic, the TPS84410 produces a regulated output voltage following the application of a valid input voltage. During the power-up, internal soft-start circuitry slows the rate that the output voltage rises, thereby limiting the amount of in-rush current that can be drawn from the input source. The soft-start circuitry introduces a short time delay from the point that a valid input voltage is recognized. Figure 21 shows the start-up waveforms for a TPS84410, operating from a 5-V input and with the output voltage adjusted to 1.8 V. The waveform is measured with a 2-A constant current load.

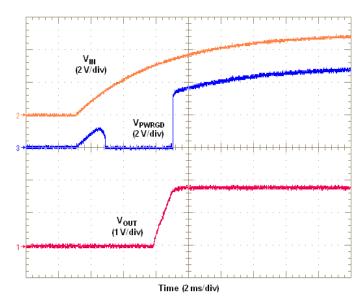


Figure 21. Start-Up Waveforms

#### 6.7 Remote Sense

The SENSE+ pin must be connected to V<sub>OUT</sub> at the load, or at the device pins.

Connecting the SENSE+ pin to  $V_{OUT}$  at the load improves the load regulation performance of the device by allowing it to compensate for any I-R voltage drop between its output pins and the load. An I-R drop is caused by the high output current flowing through the small amount of pin and trace resistance. This should be limited to a maximum of 300 mV.

#### NOTE

The remote sense feature is not designed to compensate for the forward drop of nonlinear or frequency dependent components that may be placed in series with the converter output. Examples include OR-ing diodes, filter inductors, ferrite beads, and fuses. When these components are enclosed by the SENSE+ connection, they are effectively placed inside the regulation control loop, which can adversely affect the stability of the regulator.



### 6.8 Output On/Off Inhibit (INH)

The INH pin provides electrical on/off control of the device. Once the INH pin voltage exceeds the threshold voltage, the device starts operation. If the INH pin voltage is pulled below the threshold voltage, the regulator stops switching and enters low quiescent current state.

The INH pin has an internal pull-up current source, allowing the user to float the INH pin for enabling the device. If an application requires controlling the INH pin, use an open drain/collector device, or a suitable logic gate to interface with the pin. Do not place an external pull-up resistor on this pin. Figure 22 shows the typical application of the inhibit function.

Turning Q1 on applies a low voltage to the inhibit control (INH) pin and disables the output of the supply, as shown in Figure 23. If Q1 is turned off, the supply executes a soft-start power-up sequence, as shown in Figure 24. The waveforms were measured with a 2-A constant current load.

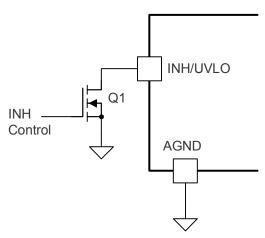
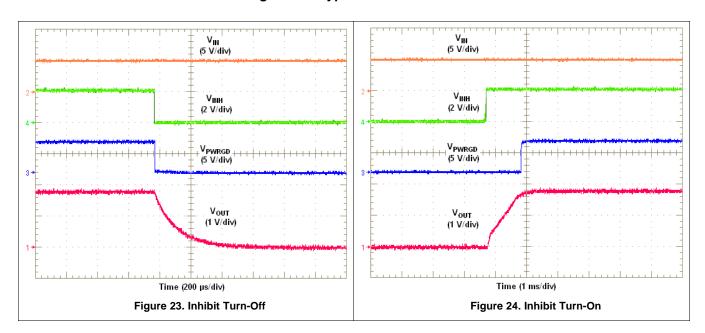


Figure 22. Typical Inhibit Control





### 6.9 Slow Start (SS/TR)

Connecting the STSEL pin to AGND and leaving SS/TR pin open enables the internal SS capacitor with a slow start interval of approximately 1.1 ms. Adding additional capacitance between the SS pin and AGND increases the slow start time. Table 7 shows an additional SS capacitor connected to the SS/TR pin and the STSEL pin connected to AGND. See Table 7 below for SS capacitor values and timing interval.

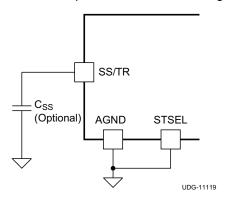


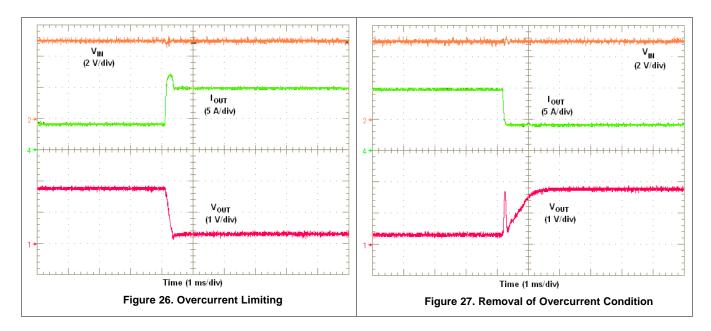
Figure 25. Slow-Start Capacitor (C<sub>SS</sub>) and STSEL Connection

Table 7. Slow-Start Capacitor Values and Slow-Start Time

C <sub>SS</sub> (pF)	open	2200	4700	10000	15000	22000	25000
SS Time (msec)	1.1	1.9	2.8	4.6	6.4	8.8	9.8

#### 6.10 Overcurrent Protection

For protection against load faults, the TPS84410 uses current limiting. The device is protected from overcurrent conditions by cycle-by-cycle current limiting and frequency foldback. During an overcurrent condition the output current is limited and the output voltage is reduced, as shown in Figure 26. When the overcurrent condition is removed, the output voltage returns to the established voltage, as shown in Figure 27.



RT/CLK

AGND



### 6.11 Synchronization (CLK)

An internal phase locked loop (PLL) has been implemented to allow synchronization between 500 kHz and 2 MHz, and to easily switch from RT mode to CLK mode. To implement the synchronization feature, connect a square wave clock signal to the RT/CLK pin with a minimum pulse width of 75 ns. The maximum clock pulse width must be calculated using Equation 2. The clock signal amplitude must transition lower than 0.4 V and higher than 2.2 V. The start of the switching cycle is synchronized to the falling edge of RT/CLK pin. In applications where both RT mode and CLK mode are needed, the device can be configured as shown in Figure 28.

Before the external clock is present, the device works in RT mode and the switching frequency is set by RT resistor ( $R_{RT}$ ). When the external clock is present, the CLK mode overrides the RT mode. The device switches from RT mode to CLK mode and the RT/CLK pin becomes high impedance as the PLL starts to lock onto the frequency of the external clock. The device will lock to the external clock frequency approximately 15  $\mu$ s after a valid clock signal is present. It is not recommended to switch from CLK mode back to RT mode because the internal switching frequency drops to a lower frequency before returning to the switching frequency set by the RT resistor.

$$CLK_PW_{MAX} = \frac{0.75 \times \left(1 - \frac{V_{OUT}}{V_{IN(min)}}\right)}{f_{SW}}$$

$$(2)$$
500 kHz to 2 MHz External Clock

Figure 28. CLK/RT Configuration

The synchronization frequency must be selected based on the output voltages of the devices being synchronized. Table 8 shows the allowable frequencies for a given range of output voltages based on a resistive load. 5V input applications requiring 3.5A or less can synchronize to a wider frequency range. For the most efficient solution, always synchronize to the lowest allowable frequency. For example, an application requires synchronizing three TPS84410 devices with output voltages of 1.2V@3.7A, 1.8@2.5AV and 3.3V@ 2.1A, all powered from VIN = 5V. Table 8 shows that all three output voltages can be synchronized to any frequency between 750 kHz to 1 MHz. For best efficiency, choose 750 kHz as the sychronization frequency.

Table 8. Synchronization Frequency vs Output Voltage

			VIN	VIN = 3.3 V				
SYNCHRONIZATION	R <sub>RT</sub>	I <sub>OUT</sub> ≤	3.5 A	I <sub>OUT</sub> >	> 3.5 A	All I <sub>OUT</sub> V <sub>OUT</sub> RANGE (V)		
FREQUENCY (kHz)	$(k\Omega)$	V <sub>OUT</sub> RA	NGE (V)	V <sub>OUT</sub> RA	ANGE (V)			
		MIN	MAX	MIN	MAX	MIN	MAX	
500	open	0.8	1.4	0.8	1.0	0.8	2.2	
550	3400	0.8	1.6	0.8	1.1	0.8	2.4	
600	1800	0.8	1.8	0.8	1.2	0.8	2.5	
650	1200	0.8	2.1	0.8	1.4	0.8	2.5	
700	887	0.8	2.6	0.8	1.6	0.8	2.5	
750	715	0.9	3.6	0.9	1.8	0.8	2.5	
800	590	0.9	3.6	0.9	2.1	0.8	2.5	
900	511	1.0	3.6	1.0	3.6	0.8	2.5	
1000	348	1.2	3.6	1.2	3.6	0.8	2.4	
1250	232	1.4	3.6	1.4	3.6	1.0	2.4	
1500	174	1.7	3.6	1.7	3.6	1.1	2.3	
1750	137	2.0	3.6	2.0	3.6	1.3	2.2	



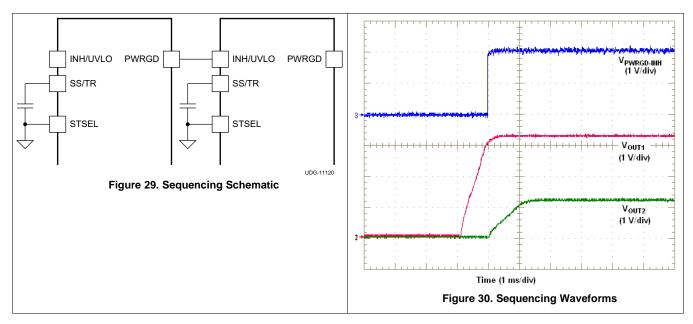
## Table 8. Synchronization Frequency vs Output Voltage (continued)

SYNCHRONIZATION FREQUENCY (kHz)	R <sub>RT</sub> (kΩ)		VIN :	VIN = 3.3 V				
		I <sub>OUT</sub> ≤	3.5 A	I <sub>OUT</sub> >	3.5 A	All I <sub>OUT</sub>		
		V <sub>OUT</sub> RA	NGE (V)	V <sub>OUT</sub> RA	NGE (V)	V <sub>OUT</sub> RANGE (V)		
		MIN	MAX	MIN	MAX	MIN	MAX	
2000	113	2.3	3.4	2.3	2.3 3.3		2.2	



### 6.12 Sequencing (SS/TR)

Many of the common power supply sequencing methods can be implemented using the SS/TR, INH and PWRGD pins. The sequential method is illustrated in Figure 29 using two TPS84410 devices. The PWRGD pin of the first device is coupled to the INH pin of the second device which enables the second power supply once the primary supply reaches regulation. Do not place a pull-up resistor on PWRGD in this configuration. Figure 30 shows sequential turn-on waveforms of two TPS84410 devices.

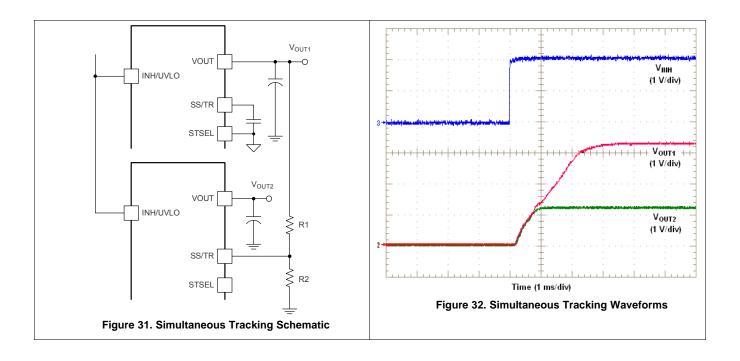


Simultaneous power supply sequencing can be implemented by connecting the resistor network of R1 and R2 shown in Figure 31 to the output of the power supply that needs to be tracked or to another voltage reference source. Figure 32 shows simultaneous turn-on waveforms of two TPS84410 devices. Use Equation 3 and Equation 4 to calculate the values of R1 and R2.

$$R1 = \frac{(V_{OUT2} \times 12.6)}{0.803} (k\Omega)$$

$$R2 = \frac{0.803 \times R1}{(V_{OUT2} - 0.803)} (k\Omega)$$
(4)







### 6.13 Programmable Undervoltage Lockout (UVLO)

The TPS84410 implements internal UVLO circuitry on the VIN pin. The device is disabled when the VIN pin voltage falls below the internal VIN UVLO threshold. The internal VIN UVLO rising threshold is 3.135 V (max) with a typical hysteresis of 300 mV.

If an application requires a higher UVLO threshold on the VIN pin, the UVLO pin can be configured as shown in Figure 33. Table 9 lists standard values for  $R_{UVLO}$  to adjust the VIN UVLO voltage up.

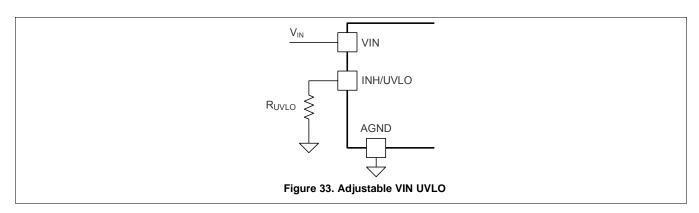


Table 9. Standard Resistor values for Adjusting VIN UVLO

VIN UVLO (V) (typ)	3.25	3.5	3.75	4.0	4.25	4.5	4.75
$R_{UVLO}\left(k\Omega\right)$	294	133	86.6	63.4	49.9	42.2	35.7
Hysteresis (mV)	325	335	345	355	365	375	385

#### 6.14 Thermal Shutdown

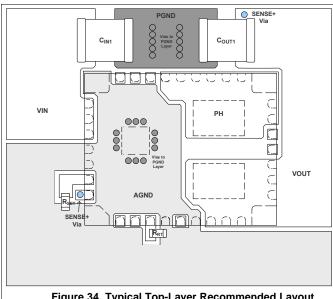
The internal thermal shutdown circuitry forces the device to stop switching if the junction temperature exceeds 175°C typically. The device reinitiates the power up sequence when the junction temperature drops below 160°C typically.



#### 6.15 Layout Guidelines

To achieve optimal electrical and thermal performance, an optimized PCB layout is required. Figure 34, shows a typical PCB layout. Some considerations for an optimized layout are:

- Use large copper areas for power planes (VIN, VOUT, and PGND) to minimize conduction loss and thermal stress.
- Place ceramic input and output capacitors close to the module pins to minimize high frequency noise.
- Locate additional output capacitors between the ceramic capacitor and the load.
- Place a dedicated AGND copper area beneath the TPS84410.
- Connect the AGND and PGND copper area at one point; directly at the pin 37 PowerPad using multiple vias.
- Place  $R_{SET}$ ,  $R_{RT}$ , and  $C_{SS}$  as close as possible to their respective pins.
- Use multiple vias to connect the power planes to internal layers.



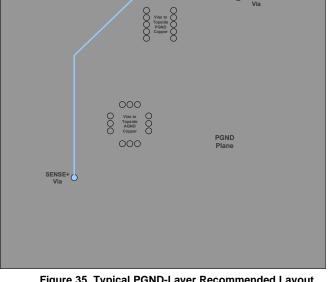


Figure 34. Typical Top-Layer Recommended Layout

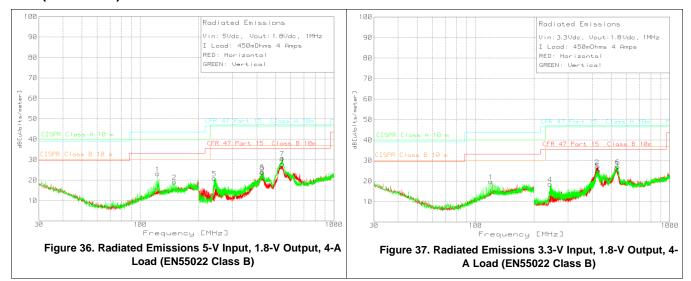
Figure 35. Typical PGND-Layer Recommended Layout

#### 6.16 EMI

The TPS84410 is compliant with EN55022 Class B radiated emissions. Figure 36 and Figure 37 show typical examples of radiated emissions plots for the TPS84410 operating from 5V and 3.3V respectively. Both graphs include the plots of the antenna in the horizontal and vertical positions.



### **EMI** (continued)





## 7 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (June 2017) to Revision C	Page
Increased the peak reflow temperature and maximum number of reflows to JEDEC spec manufacturability	·
• 已添加 <i>器件和文档支持</i> 部分	
• 已添加 机械、封装和可订购信息 部分	27
Changes from Revision A (March 2012) to Revision B	Page
Changes from Revision A (March 2012) to Revision B  Added peak reflow and maximum number of reflows information	
,	



### 8 器件和文档支持

### 8.1 接收文档更新通知

要接收文档更新通知,请导航至 Tl.com 上的器件产品文件夹。单击右上角的通知我 进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

### 8.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的 《使用条款》。

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设计支持 TI 参考设计支持 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

#### 8.3 商标

E2E is a trademark of Texas Instruments.

### 8.4 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

#### 8.5 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、缩写和定义。

### 9 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且 不会对此文档进行修订。如需获取此数据表的浏览器版本,请参阅左侧的导航栏。



### PACKAGE OPTION ADDENDUM

4-Jun-2020

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS84410RKGR	ACTIVE	B1QFN	RKG	39	500	RoHS Exempt & Green	NIPDAU	Level-3-250C-168 HR	-40 to 85	TPS84410	Samples
TPS84410RKGT	ACTIVE	B1QFN	RKG	39	250	RoHS Exempt & Green	NIPDAU	Level-3-250C-168 HR	-40 to 85	TPS84410	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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4-Jun-2020

## PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

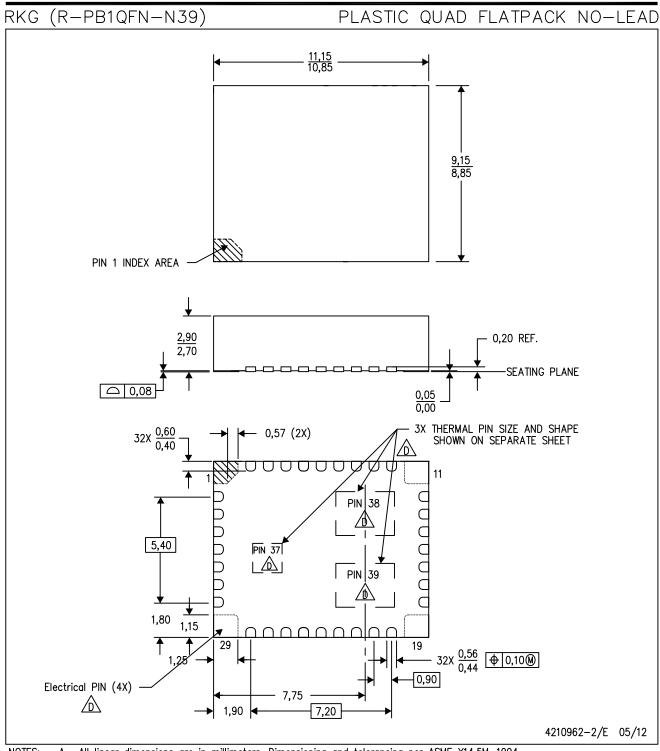
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS84410RKGR	B1QFN	RKG	39	500	330.0	24.4	9.35	11.35	3.1	16.0	24.0	Q1
TPS84410RKGT	B1QFN	RKG	39	250	330.0	24.4	9.35	11.35	3.1	16.0	24.0	Q1

www.ti.com 10-Mar-2021



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS84410RKGR	B1QFN	RKG	39	500	383.0	353.0	58.0
TPS84410RKGT	B1QFN	RKG	39	250	383.0	353.0	58.0



- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Quad Flatpack, No-leads (QFN) package configuration.
  - 1 The package thermal pad must be soldered to the board for thermal and mechanical performance.
    - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
  - $\sqrt{F}$ .\ The package thermal performance may be enhanced by bonding the thermal pad to an external thermal plane.



## RKG (R-PQFN-N39)

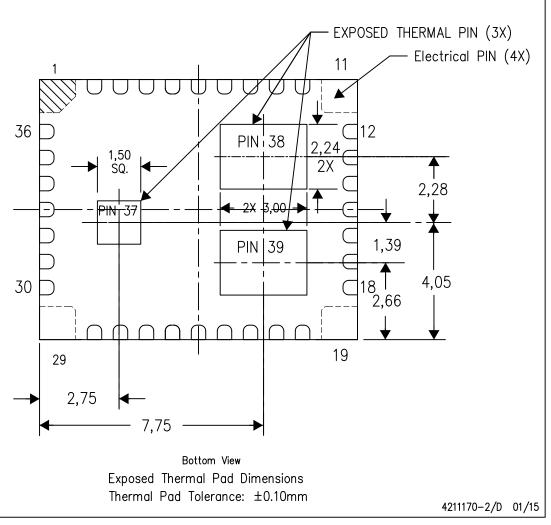
## PLASTIC QUAD FLATPACK NO-LEAD

#### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

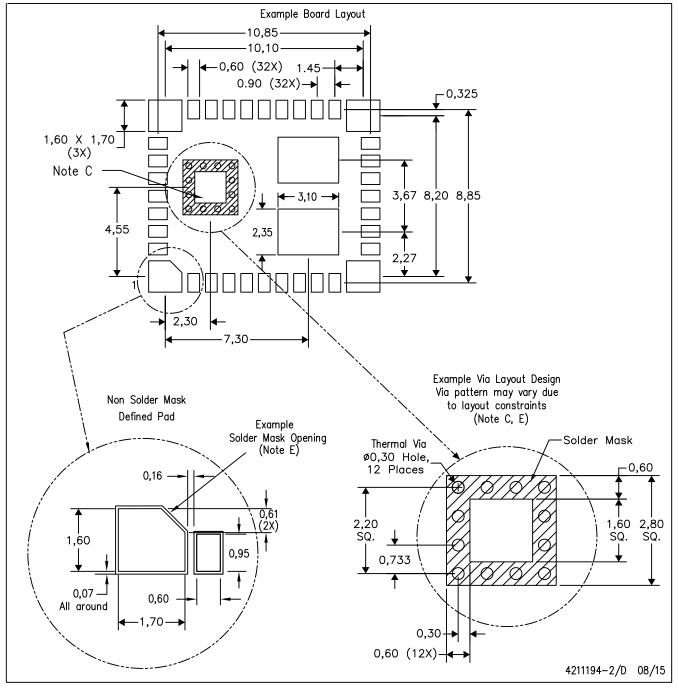
The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: A. All linear dimensions are in millimeters

## RKG (S-PB1QFN-N39)

## PLASTIC QUAD FLATPACK NO-LEAD



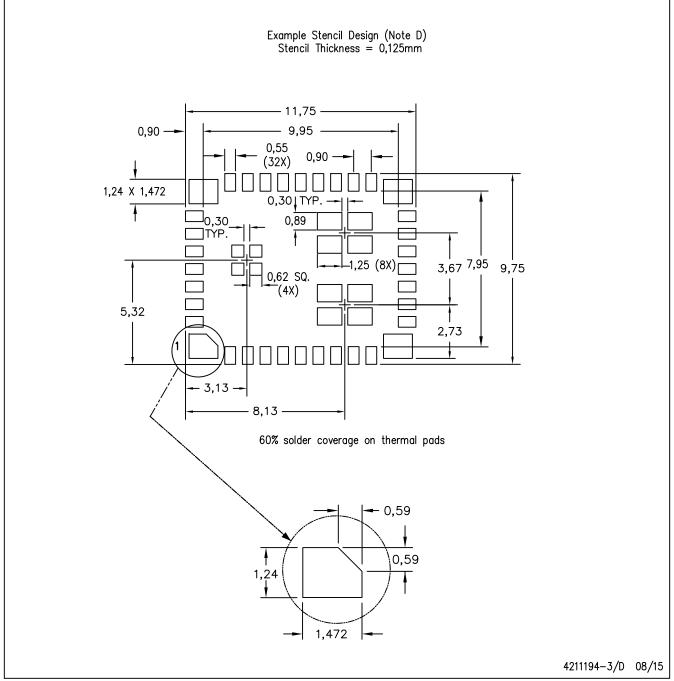
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- E. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



## RKG (S-PB1QFN-N39)

## PLASTIC QUAD FLATPACK NO-LEAD



NOTES: All linear dimensions are in millimeters.

- This drawing is subject to change without notice.
- This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.

  E. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



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